

ABSTRACT

A semiconductor device includes an SRAM section and a logic circuit section formed on a single semiconductor substrate.

5 First and second gate electrode layers located in a first conductive layer, first and second drain-drain contact layers located in a second conductive layer, first and second drain-gate contact layers located in a third conductive layer become conductive layers for forming a flip-flop of the SRAM section. The logic circuit section has no wiring layer at the same level as the first and second drain-drain contact layers.

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